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# Standard Recovery Diodes (MAGN-A-PAK Power Modules), 250 A to 320 A



**MAGN-A-PAK** 

PRIMARY CHARACTERISTICS							
I <sub>F(AV)</sub>	250 A to 320 A						
Type	Modules - diode, high voltage						
Package	MAGN-A-PAK						
Circuit configuration	Two diodes doubler circuit, two diodes common cathode, single diode						

#### **FEATURES**

- · High voltage
- · Electrically isolated base plate
- 3000 V<sub>RMS</sub> isolating voltage
- Industrial standard package
- · Simplified mechanical designs, rapid assembly
- · High surge capability
- · Large creepage distances
- UL approved file E78996
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **DESCRIPTION / APPLICATIONS**

This VS-VSK series of MAGN-A-PAKs uses high voltage power diodes in two basic configurations. The semiconductors are electrically isolated from the metal base, allowing common heatsinks and compact assemblies to be built. They can be interconnected to form single phase or three phase bridges and the single diode module can be used in conjunction with the thyristor modules as a freewheel diode.

These modules are intended for general purpose applications such as battery chargers, welders and plating equipment and where high voltage and high current are required (motor drives, etc.)

MAJOR RATINGS AND CHARACTERISTICS							
SYMBOL	CHARACTERISTICS	ERISTICS VSK.250		VSK.320	UNITS		
1		250	270	320	Α		
I <sub>F(AV)</sub>	T <sub>C</sub>	100	100	100	°C		
I <sub>F(RMS)</sub>		393	424	502			
	50 Hz	7015	8920	10 110	Α		
IFSM	60 Hz	7345	9430	10 580			
l <sup>2</sup> t	50 Hz	246	398	511	1.42-		
1-1	60 Hz	225	363	466	kA <sup>2</sup> s		
I <sup>2</sup> √t		2460	3980	5110	kA²√s		
V <sub>RRM</sub>		400 to 2000	400 to 3000	400 to 2000	V		
TJ			-40 to +150	•	°C		



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### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS										
TYPE NUMBER	VOLTAGE CODE	V <sub>RRM,</sub> MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I <sub>RRM</sub> MAXIMUM AT 150 °C mA						
VS-VSK.270 VS-VSK.320	04	400	500							
	08	800	900							
VS-VSK.250 VS-VSK.270	12	1200	1300	50						
VS-VSK.270 VS-VSK.320	16	1600	1700							
20		2000	2100							
VS-VSK.270	30	3000	3100							

FORWARD CONDUCTION								
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES			UNITS
PANAMETER	STWIBOL	SE TEST CONDITIONS		VSK.250	VSK.270	VSK.320	ONTO	
Maximum average forward	I <sub>F(AV)</sub>	180° cond	uction, half sin	e wave	250	270	320	Α
current at case temperature	. (/ (*/		,		100	100	100	°C
Maximum RMS forward current	I <sub>F(RMS)</sub>	As AC swit	tch		393	424	502	
		t = 10 ms	No voltage		7015	8920	10 110	
Maximum peak, one-cycle forward,		t = 8.3 ms	reapplied	Sinusoidal half wave,	7345	9340	10 580	Α
non-repetitive surge current	I <sub>FSM</sub>	t = 10 ms	100 %		5900	7500	8500	
		t = 8.3 ms	V <sub>RRM</sub> reapplied		6180	7850	8900	
	l <sup>2</sup> t	t = 10 ms	No voltage	initial $T_J = T_J maximum$	246	398	511	- kA <sup>2</sup> s
NA - view ver 124 favr fi veire e		t = 8.3 ms	reapplied		225	363	466	
Maximum I <sup>2</sup> t for fusing	1-1	t = 10 ms	100 %		174	281	361	
		t = 8.3 ms	V <sub>RRM</sub> reapplied		159	257	330	
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t	t = 0.1 ms	to 10 ms, no v	oltage reapplied	2460	3980	5110	kA²√s
Low level value of threshold voltage	V <sub>F(TO)1</sub>	$(16.7 \% x)^2$ $T_J = T_J ma$	$\pi \times I_{F(AV)} < I < \pi$ eximum	0.79	0.74	0.69	V	
High level value of threshold voltage	V <sub>F(TO)2</sub>	$(I > \pi \times I_{F(AV)}), T_J = T_J \text{ maximum}$			0.92	0.87	0.86	
Low level forward slope resistance	r <sub>f1</sub>	(16.7 % x $\pi$ x $I_{F(AV)}$ < $I$ < $\pi$ x $I_{F(AV)}$ ), $T_J = T_J$ maximum			0.63	0.94	0.59	mΩ
High level forward slope resistance	r <sub>f2</sub>	$(I > \pi \times I_{F(AV)}), T_J = T_J \text{ maximum}$			0.49	0.81	0.44	
Maximum forward voltage drop	V <sub>FM</sub>			ximum, 180° conduction : I <sub>F(AV)</sub> + r <sub>f</sub> x (I <sub>F(RMS)</sub> ) <sup>2</sup>	1.29	1.48	1.28	V

BLOCKING										
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS						
Maximum peak reverse leakage current	I <sub>RRM</sub>	T <sub>J</sub> = 150 °C	50	mA						
RMS insulation voltage	V <sub>INS</sub>	50 Hz, circuit to base, all terminals shorted, t = 1 s	3000	V						



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THERMAL AND MECHANICAL SPECIFICATIONS									
DADAMETED		SYMBOL	TEST CONDITIONS		UNITS				
PARAMETER			VSK.250	VSK.270	VSK.320	UNITS			
Maximum junction operating and storage temperature range		T <sub>J</sub> , T <sub>Stg</sub>		-40 to +150		°C			
	Maximum thermal resistance, junction to case per junction R <sub>thJC</sub>		DC operation	0.16	0.125	0.125	K/W		
Maximum resistance, case to heat sink per module		R <sub>thCS</sub>	Mounting surface flat, smooth and greased	0.035		1000			
Mounting MA	AGN-A-PAK to heatsink	A mounting compound is recommended and the torque should be rechecked		4 to 6		Nm			
4	usbar to MAGN-A-PAK		after a period of about 3 hours to allow for the spread of the compound.		4 10 0		INIII		
Approximate weight					800		g		
Approximate we	Approximate weight				30		oz.		
Case style	style MAGN-A-PAK		A-PAK						

AR CONDUCTION PER JUNCTION											
DEVICE			DAL COND					ULAR CON	NDUCTION UM		UNITS
	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	
VSK.250	0.009	0.010	0.014	0.020	0.032	0.007	0.011	0.015	0.021	0.033	
VSK.270	0.008	0.012	0.014	0.020	0.032	0.007	0.011	0.015	0.020	0.033	K/W
VSK.320	0.008	0.010	0.013	0.020	0.032	0.007	0.011	0.015	0.020	0.033	

#### Note

The table above shows the increment of thermal resistance R<sub>thJC</sub> when devices operate at different conduction angles than DC

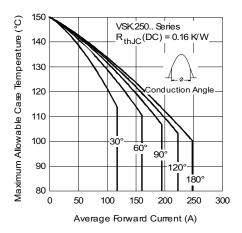


Fig. 1 - Current Ratings Characteristics

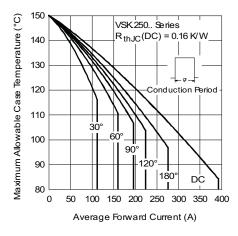


Fig. 2 - Current Ratings Characteristics

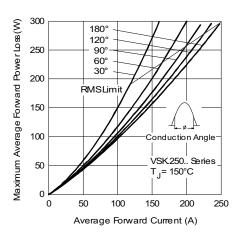


Fig. 3 - Forward Power Loss Characteristics

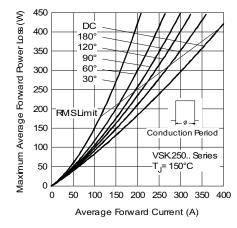


Fig. 4 - Forward Power Loss Characteristics

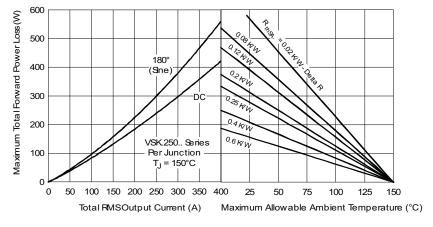


Fig. 5 - Forward Power Loss Characteristics

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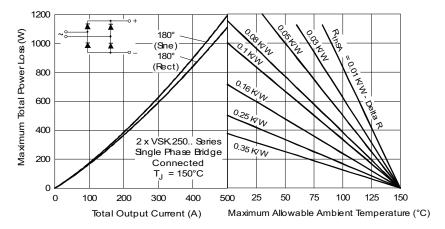


Fig. 6 - Forward Power Loss Characteristics

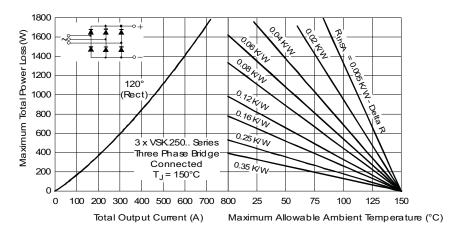


Fig. 7 - Forward Power Loss Characteristics

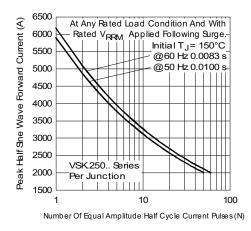


Fig. 8 - Maximum Non-Repetitive Surge Current

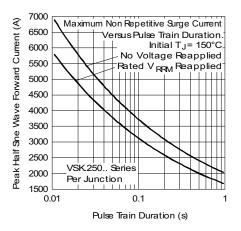


Fig. 9 - Maximum Non-Repetitive Surge Current

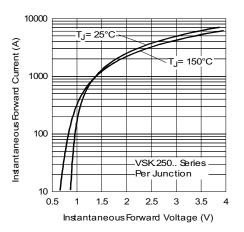


Fig. 10 - Forward Voltage Drop Characteristics

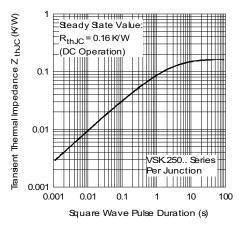


Fig. 11 - Thermal Impedance Z<sub>thJC</sub> Characteristics

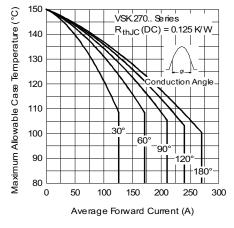


Fig. 12 - Current Ratings Characteristics

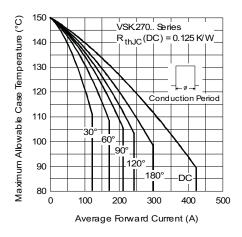


Fig. 13 - Current Ratings Characteristics

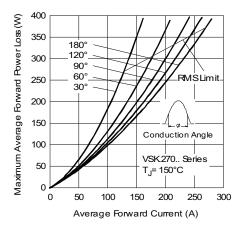


Fig. 14 - Forward Power Loss Characteristics

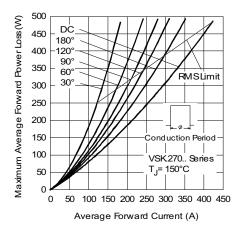


Fig. 15 - Forward Power Loss Characteristics

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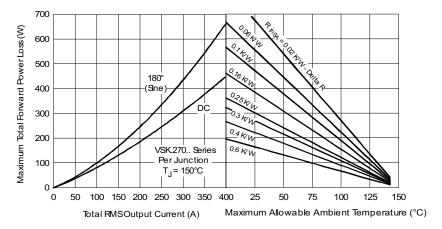


Fig. 16 - Forward Power Loss Characteristics

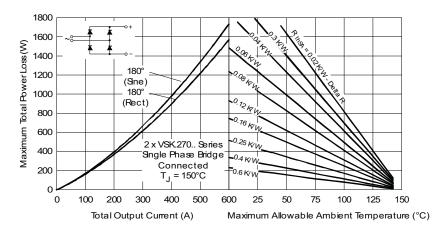


Fig. 17 - Forward Power Loss Characteristics

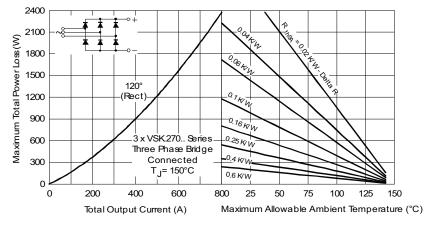


Fig. 18 - Forward Power Loss Characteristics

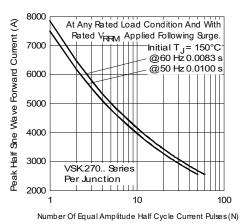
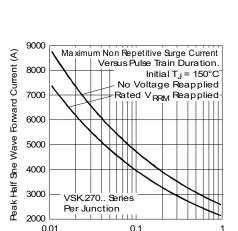


Fig. 19 - Maximum Non-Repetitive Surge Current



Pulse Train Duration (s)
Fig. 20 - Maximum Non-Repetitive Surge Current

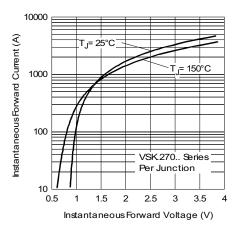


Fig. 21 - Forward Voltage Drop Characteristics

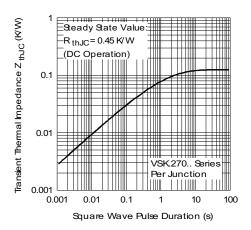


Fig. 22 - Thermal Impedance ZthJC Characteristics

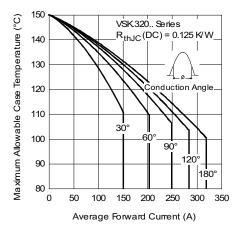


Fig. 23 - Current Ratings Characteristics

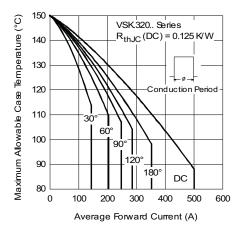


Fig. 24 - Current Ratings Characteristics

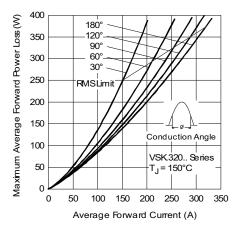


Fig. 25 - Forward Power Loss Characteristics

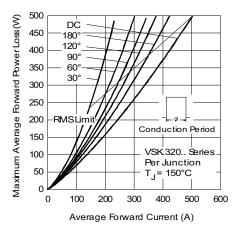


Fig. 26 - Forward Power Loss Characteristics

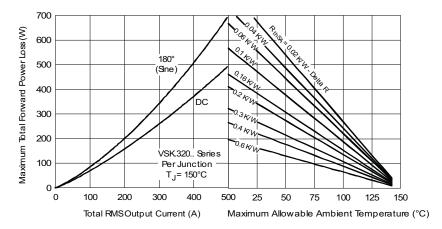


Fig. 27 - Forward Power Loss Characteristics

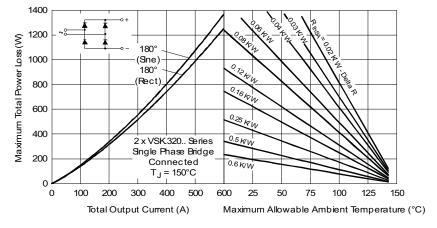


Fig. 28 - Forward Power Loss Characteristics

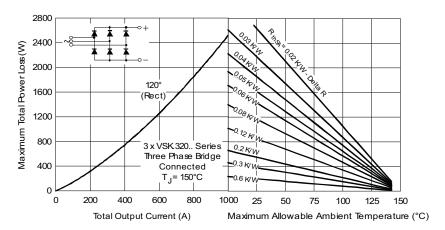


Fig. 29 - Forward Power Loss Characteristics

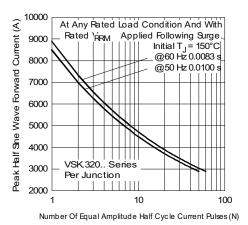


Fig. 30 - Maximum Non-Repetitive Surge Current

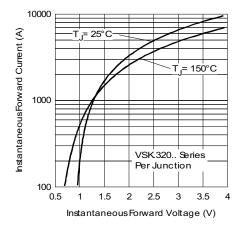


Fig. 32 - Forward Voltage Drop Characteristics

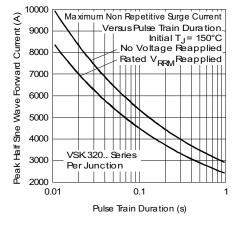


Fig. 31 - Maximum Non-Repetitive Surge Current

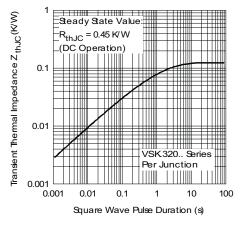
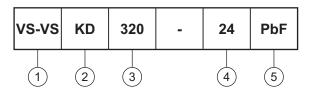


Fig. 33 - Thermal Impedance Z<sub>thJC</sub> Characteristics

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### **ORDERING INFORMATION TABLE**

Device code



- 1 Vishay Semiconductors product
- 2 Circuit configuration (see Circuit Configuration table)
- 3 Current rating: I<sub>F(AV)</sub> rounded
- 4 Voltage code x 100 = V<sub>RRM</sub> (see Voltage Ratings table)
- 5 Lead (Pb)-free

CIRCUIT DESCRIPTION	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING
		VSKD
		õ <b>†</b>
wo diodes doubler circuit	KD	~ 0 + - 0
		VSKC
		+
Two diodes common cathode	KC	+ 9 9
		VSKE
		÷ ~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~
Single diode	KE	0 + - 9

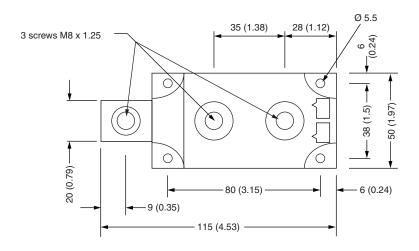
LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95086				

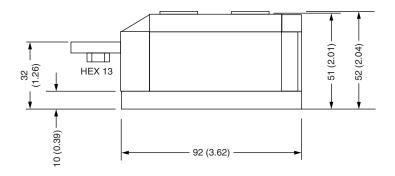


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### **MAGN-A-PAK**

### **DIMENSIONS** in millimeters (inches)





#### Notes

- Dimensions are nominal
- Full engineering drawings are available on request
- UL identification number for gate and cathode wire: UL 1385
- UL identification number for package: UL 94 V-0



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